EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	585	chalcogenide and memory and @ad<"20040203" and dielectric and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:44
S2	167	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and pore	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 11:07
S3	230	(257/2).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 16:03
S4	173	(257/2).ccls. and @ad<"20040203"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:37
S5	77	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and current and break	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 12:50
S6	11	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and current and break and test	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 12:43
S11	0	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "two chalco"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:35
S12	0	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "both chalco"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:33

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S13	20	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "first chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:37
S14	1	"upper phase change resistor"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:43
S15	15	"phase change resistor"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 14:44
S16	2	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "upper chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:05
S17	17	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "top chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 09:19
S18	19	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "second chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:07
S20	13275	horii	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:36
S21	6906	horii.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:37

S22	11	horii.in. and chalcogenide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:40
S23	5	ha.in. and chalcogenide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:12
S24	528	chalcogenide and memory and @ad<"20030720" and dielectric and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:46
S25	528	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and pd<"20030720"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:47
S27	292	chalcogenide and memory and dielectric and electrode and @pd<"20030720"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 10:37
S28	140	"phase change material" and memory and dielectric and electrode and @pd<"20030720"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 13:43
S29	86	chen.in. and chalcogenide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:22
S30	9	horii.in. and "phase change material"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:24

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S31	5	horak.in. and ("phase change material" or "chalcogenide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:25
S32	1	furkay.in. and ("phase change material" or "chalcogenide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:26
S33	155	johnson.in. and ("phase change material" or "chalcogenide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:36
S34	13	ha.in. and ("phase change material" or "chalcogenide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:38
S35	281	lee.in. and ("phase change material" or "chalcogenide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 12:38
S36	287	"memory material" and memory and dielectric and electrode and @pd<"20030720"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 13:43
S37	20	chalcogenide and memory and @ad<"20040203" and dielectric and electrode and "first chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 08:48
S38	75	chalcogenide and memory and @ad<"20030720" and (257/2).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 08:49

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S39	82	chalcogenide and @ad<"20030720" and (257/2).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 09:18
S40	87	chalcogenide and @ad<"20030720" and (257/3).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 09:43
S41	123	chalcogenide and @ad<"20030720" and (257/4,5).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 10:43
S42	121	(ovonic$ or chalcogenide) and @ad<"20030720" and (257/306, 505,246,295,200,296,748,536,103, 646,314,300,20).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 13:24
S43	441	(ovonic$ or chalcogenide) and @ad<"20030720" and ("438").clas.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 13:24
S44	2	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and "upper chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:06
S45	18	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and "second chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:55
S46	18	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and "first chalcogenide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:38

S47	445	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and two adjchalcogenide$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:39
S48	7	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and two adj chalcogenide$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:40
S49	7	chalcogenide and memory and @ad<"20030720" and dielectric and electrode and both adj chalcogenide$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 15:41
S50	387	(ovonic or chalcogenide or pcm or "phase change material") and memory and @ad<"20030720" and dielectric and electrode and (second near3 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/05 14:53
S51	182	fricke.in. and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 16:31
S52	4	("5282158" | "6061264" | "6229733" | "6512284").PN. OR ("6870751"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/09/08 16:34
S53	15	"phase change resistor"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/09 08:27
S54	95	"257".clas. and "tapered via"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/09 08:27
S55	310	(257/E27.004).ccls. and @ad<"20040203"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:37

S56	205	(257/E27.004).ccls. and @ad<"20040203" and electrode and chalcogenide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 15:38
S57	218	(ovonic or chalco$7 or pcm or "phase change material") and memory and (@ad<"20030721" or @rlad<"20030721") and (dielectric$2 or insulat$4 or oxid$6) and (second near3 chalco$7)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/05 14:57
S58	271	(ovonic or chalco$7 or pcm or "phase change material") and memory and (@ad<"20030721" or @rlad<"20030721") and (dielectric$2 or insulat$4 or oxid$6) and ((second near3 chalco$7) or (upper near3 chalco$7))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/05 14:58